



FW344A

Power MOSFET

30V, 4.5A, 64mΩ, -30V, -3.5A, 102mΩ, Complementary Dual SOIC8

ON Semiconductor®

<http://onsemi.com>

Features

- ON-resistance Nch : $R_{DS(on)1}=49m\Omega$ (typ.)
Pch : $R_{DS(on)1}=78m\Omega$ (typ.)
- 4V drive
- Halogen free compliance
- Nch+Pch MOSFET

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V_{DSS}		30	-30	V
Gate-to-Source Voltage	V_{GSS}		± 20	± 20	V
Drain Current (DC)	I_D		4.5	-3.5	A
Drain Current ($PW \leq 10\mu\text{s}$)	I_{DP}	Duty cycle $\leq 1\%$	5	-4	A
Drain Current ($PW \leq 10\mu\text{s}$)	I_{DP}	Duty cycle $\leq 1\%$	18	-14	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (2000mm ² ×0.8mm) 1unit	1.4		W
Total Dissipation	P_T	When mounted on ceramic substrate (2000mm ² ×0.8mm)	1.7		W
Channel Temperature	T_{ch}		150		$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to +150		$^\circ\text{C}$

This product is designed to "ESD immunity < 200V*", so please take care when handling.

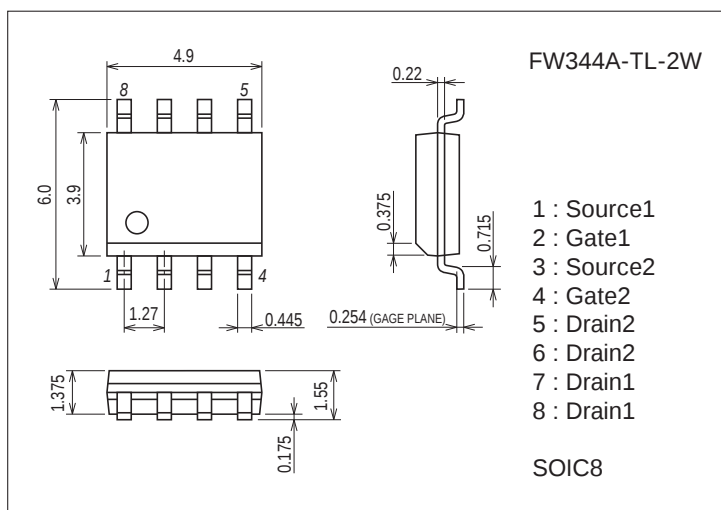
* Machine Model

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

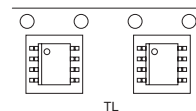
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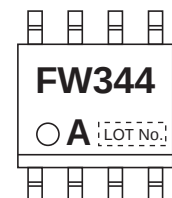
Product & Package Information

- Package : SOIC8
- JEITA, JEDEC : SC-87, SOT-96
- Minimum Packing Quantity : 2,500 pcs./reel

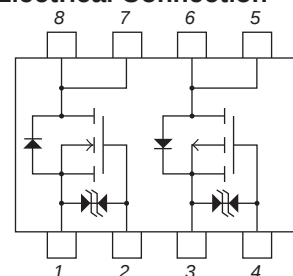
Packing Type : TL



Marking



Electrical Connection



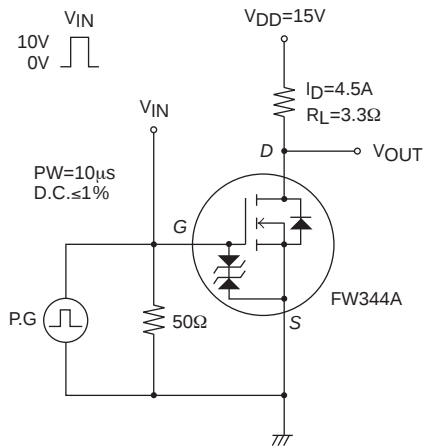
FW344A

Electrical Characteristics at Ta=25°C

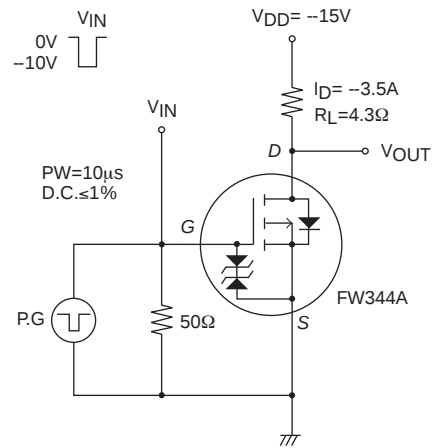
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =1mA, V _{GS} =0V	30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =4.5A		2.6		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =4.5A, V _{GS} =10V		49	64	mΩ
	R _{DS(on)2}	I _D =2A, V _{GS} =4.5V		80	112	mΩ
	R _{DS(on)3}	I _D =2A, V _{GS} =4V		100	140	mΩ
Input Capacitance	C _{iss}	V _{DS} =10V, f=1MHz		280		pF
Output Capacitance	C _{oss}			60		pF
Reverse Transfer Capacitance	C _{rss}			30		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		6		ns
Rise Time	t _r			21		ns
Turn-OFF Delay Time	t _{d(off)}			20		ns
Fall Time	t _f			10		ns
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =10V, I _D =4.5A		5.6		nC
Gate-to-Source Charge	Q _{gs}			1.2		nC
Gate-to-Drain “Miller” Charge	Q _{gd}			0.8		nC
Diode Forward Voltage	V _{SD}	I _S =4.5A, V _{GS} =0V		0.85	1.2	V
[P-channel]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0V	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-1.2		-2.3	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-3.5A		3.9		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-3.5A, V _{GS} =-10V		78	102	mΩ
	R _{DS(on)2}	I _D =-2A, V _{GS} =-4.5V		125	175	mΩ
	R _{DS(on)3}	I _D =-2A, V _{GS} =-4V		145	205	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		250		pF
Output Capacitance	C _{oss}			65		pF
Reverse Transfer Capacitance	C _{rss}			46		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		5.4		ns
Rise Time	t _r			34		ns
Turn-OFF Delay Time	t _{d(off)}			28		ns
Fall Time	t _f			24		ns
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-10V, I _D =-3.5A		5		nC
Gate-to-Source Charge	Q _{gs}			1		nC
Gate-to-Drain “Miller” Charge	Q _{gd}			1.2		nC
Diode Forward Voltage	V _{SD}	I _S =-3.5A, V _{GS} =0V		-0.88	-1.5	V

Switching Time Test Circuit

[N-channel]

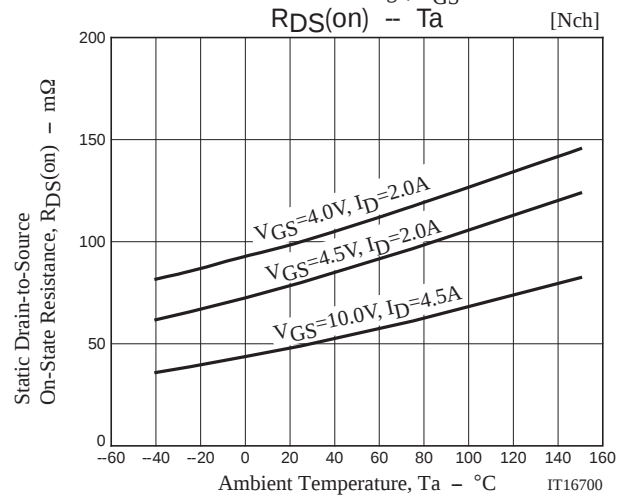
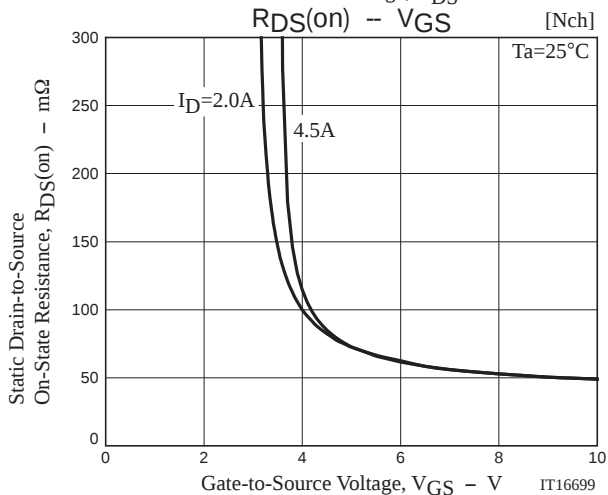
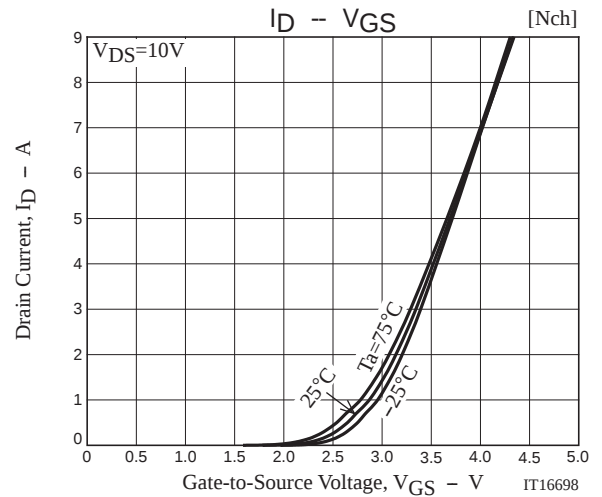
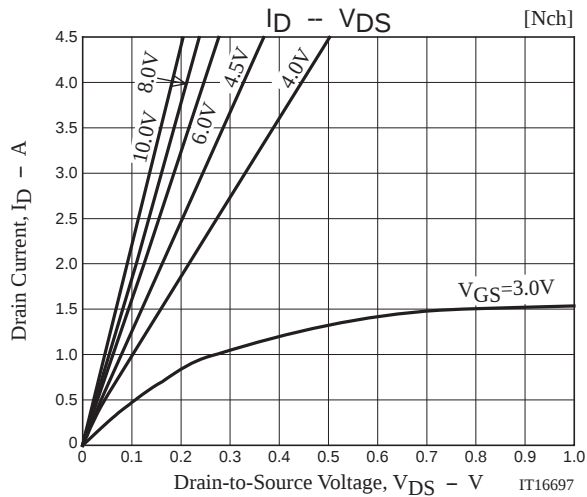


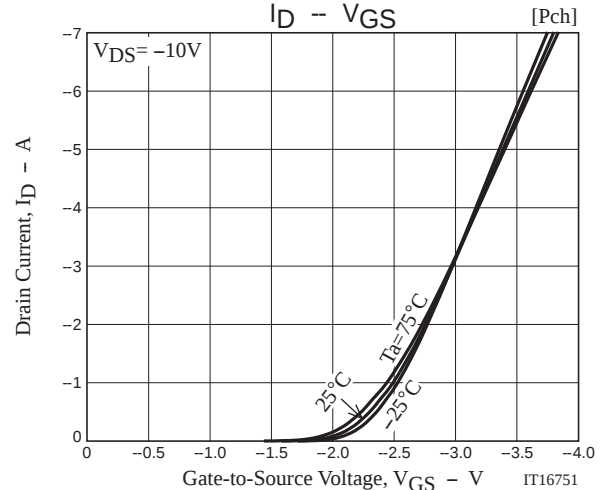
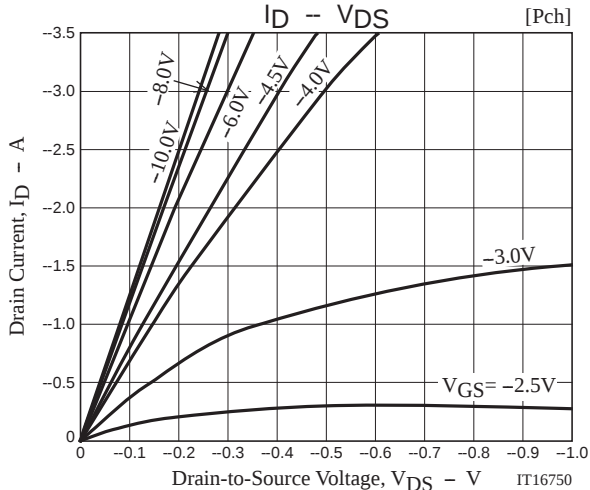
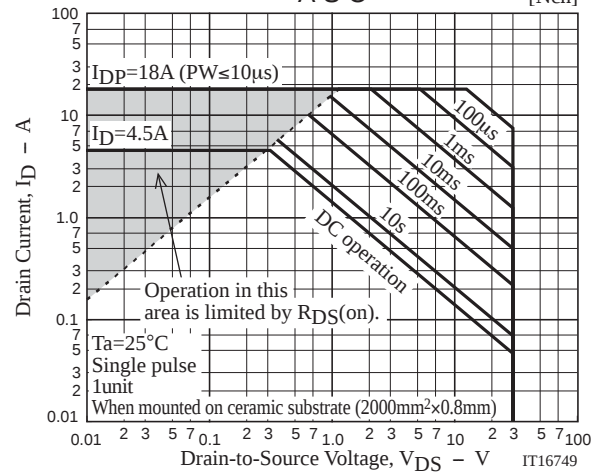
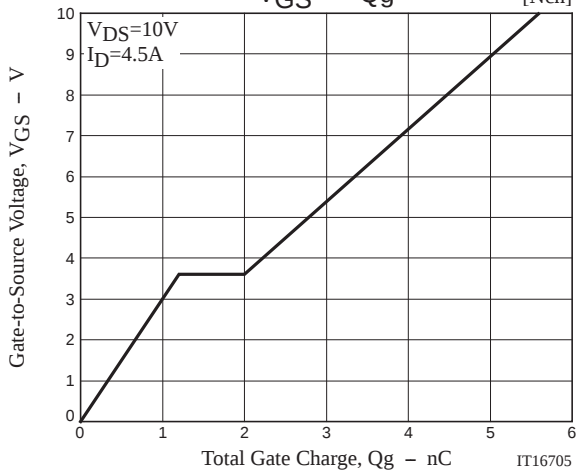
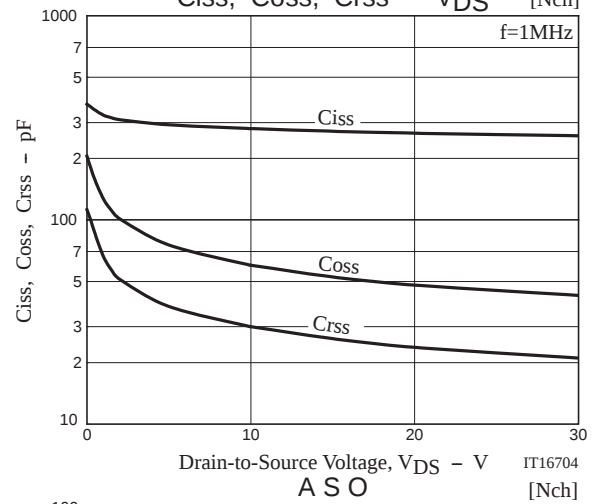
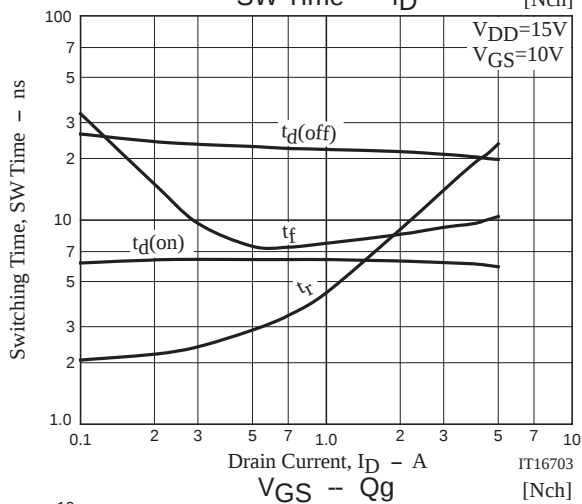
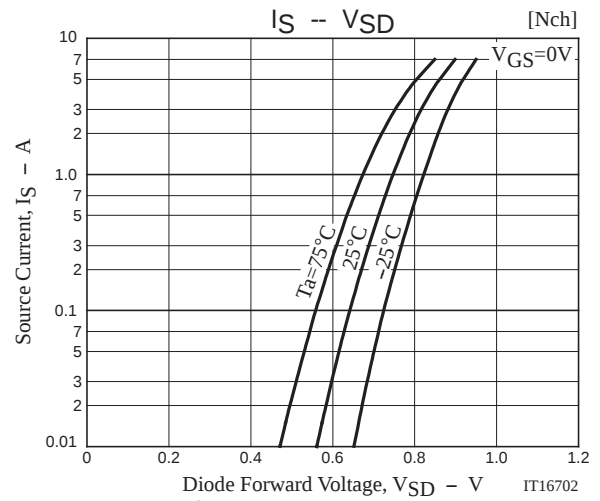
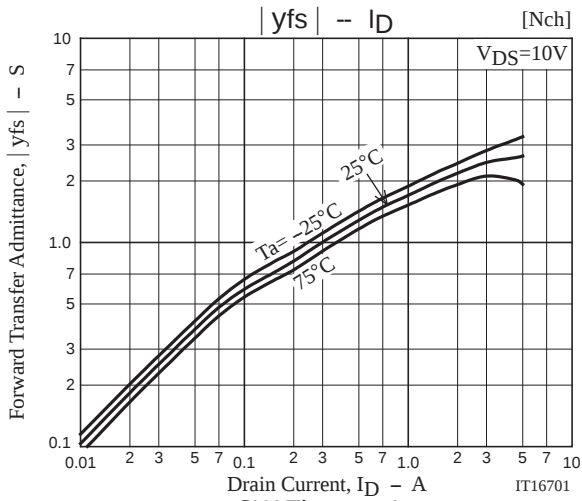
[P-channel]

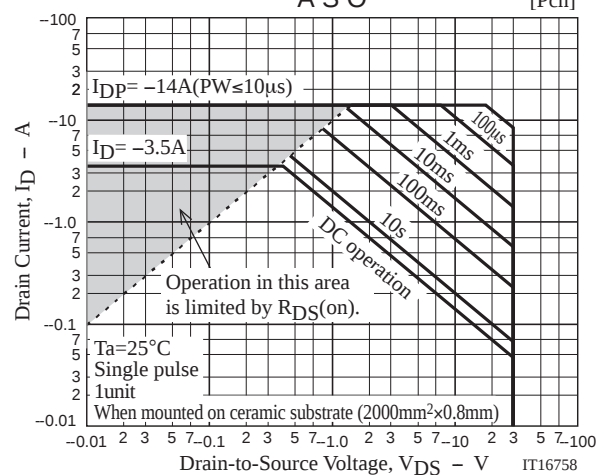
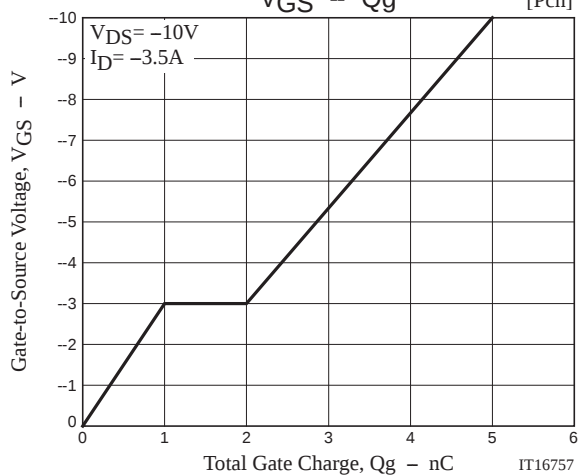
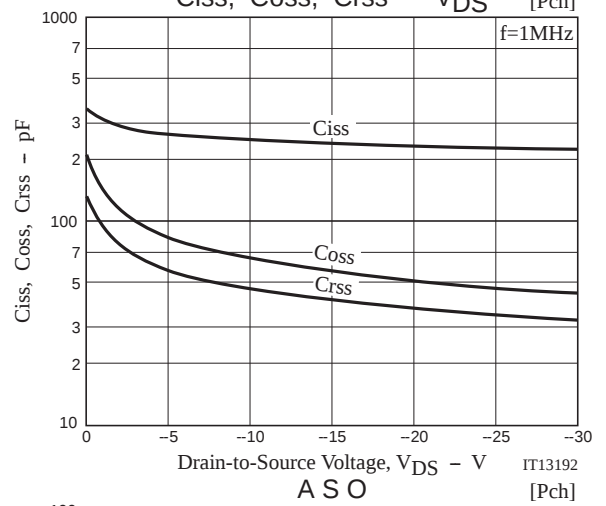
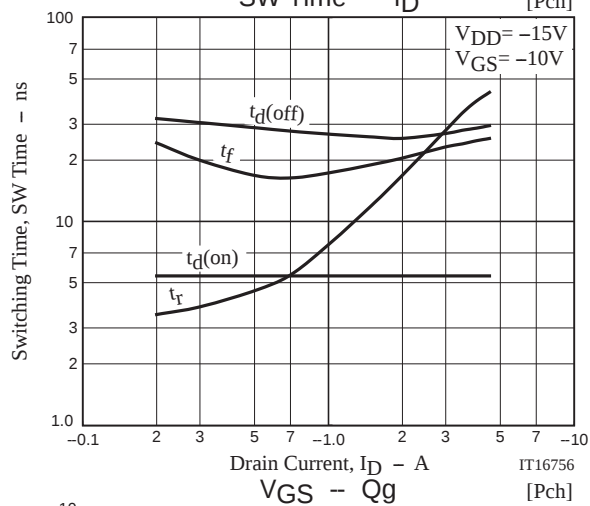
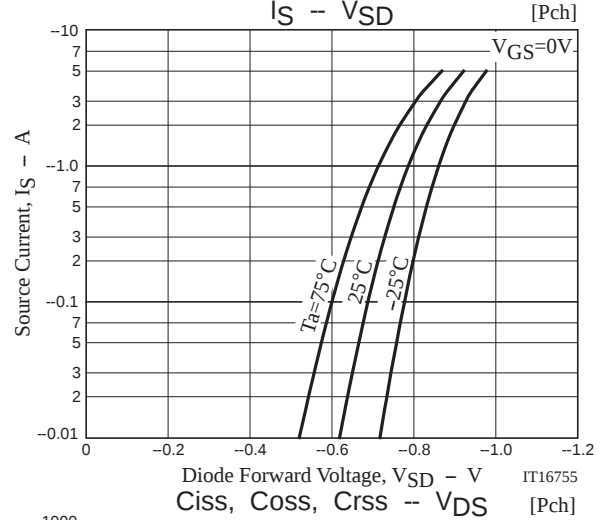
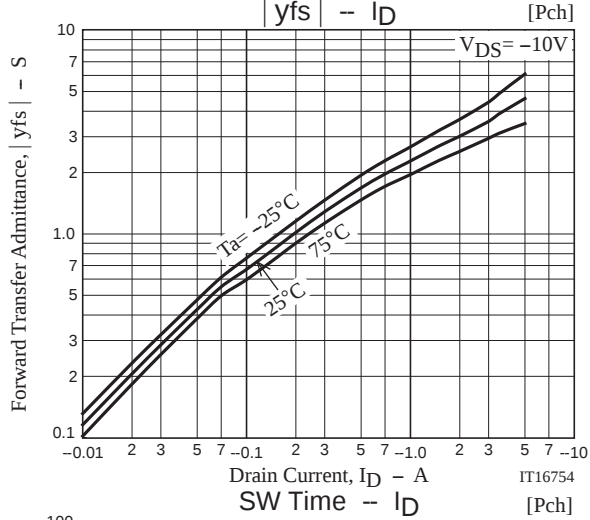
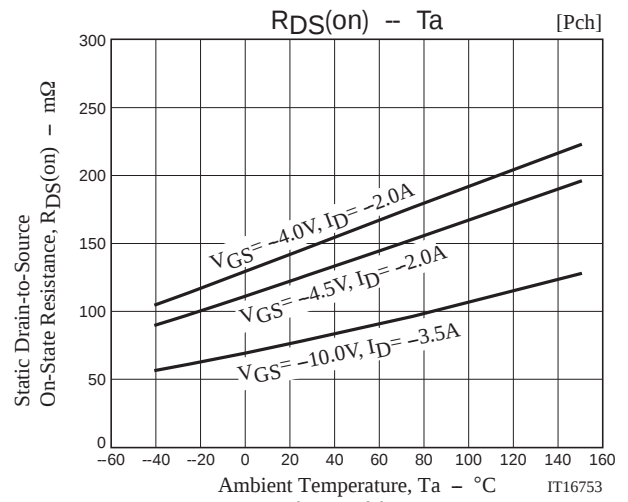
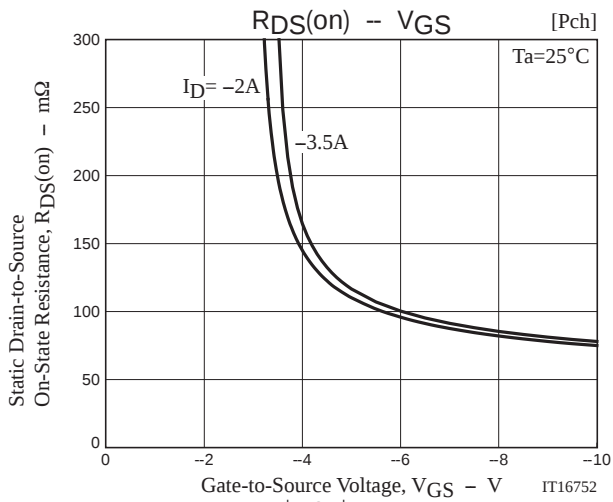


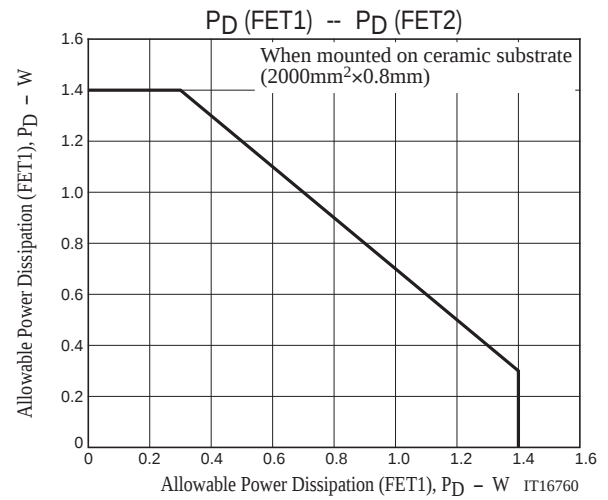
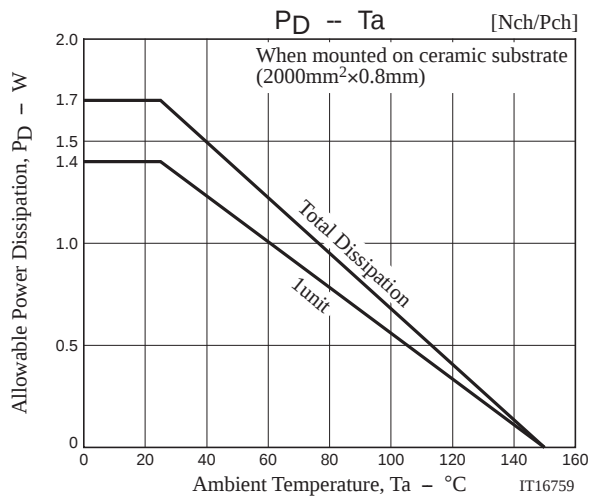
Ordering Information

Device	Package	Shipping	memo
FW344A-TL-2W	SOIC8	2,500pcs./reel	Pb Free and Halogen Free









Taping Specification

FW344A-TL-2W

1. Packing Format

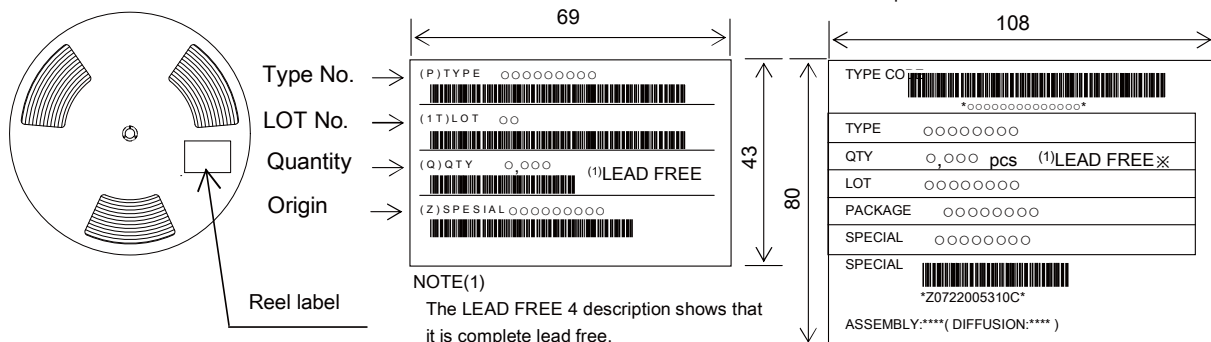
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX W206-112	Outer BOX W207-124
SOIC8	B202-101	2,500	12,500	25,000	5 reels contained Dimensions :mm(external) 340×95×340	2 inner boxes contained Dimensions :mm(external) 360×210×375

Packing method

Reel label, Inner box label (unit: mm)

Outer box label

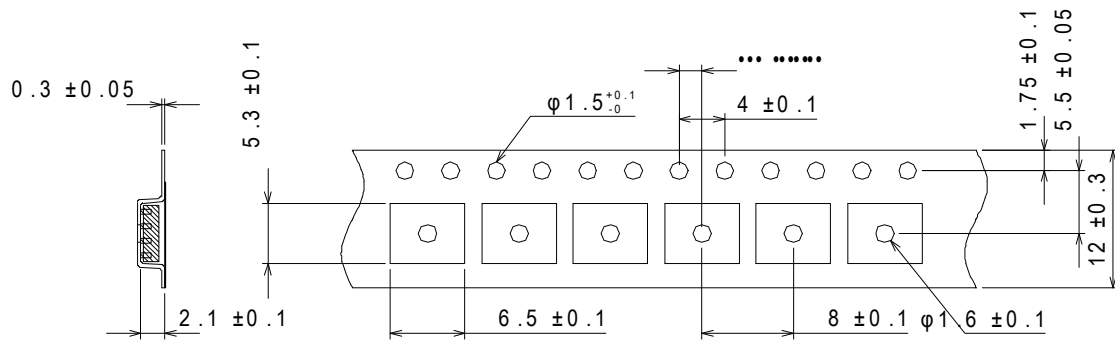
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.



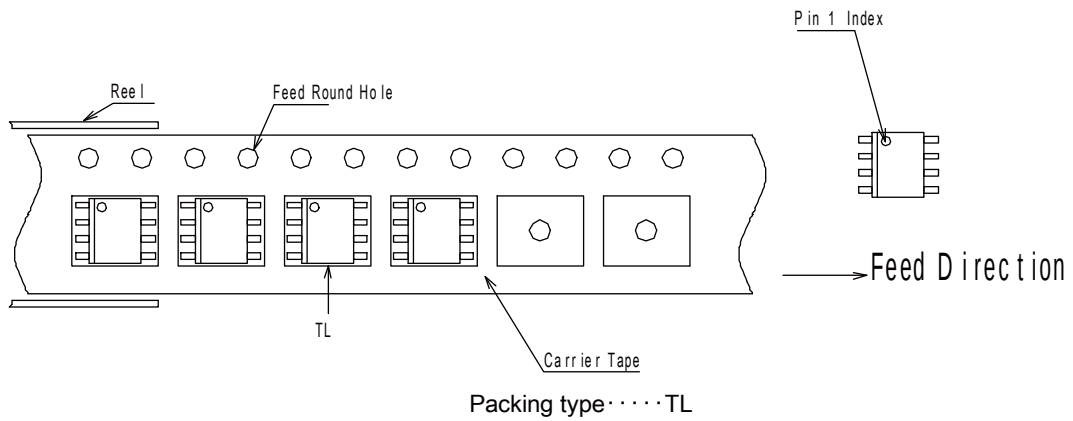
Label	JEITA Phase
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

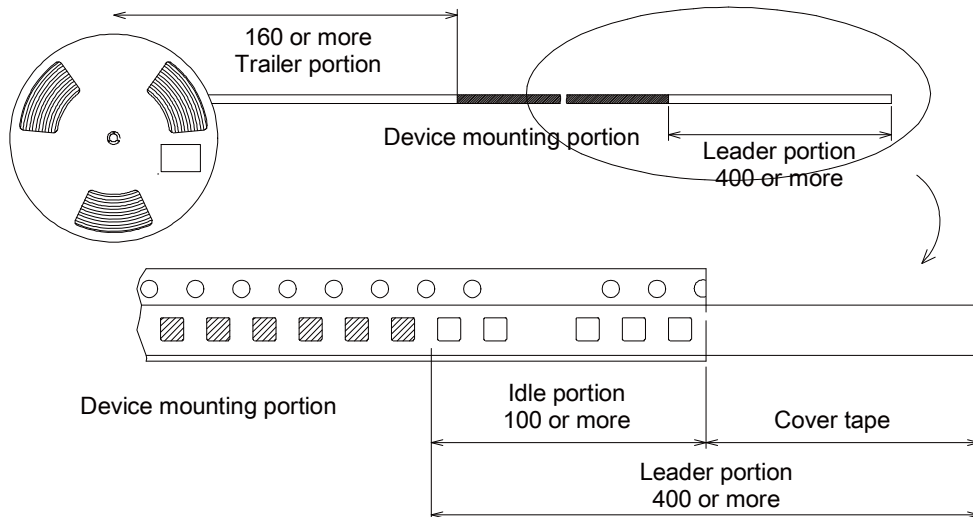
2-1. Carrier tape size (unit: mm)



2-2. Device placement direction

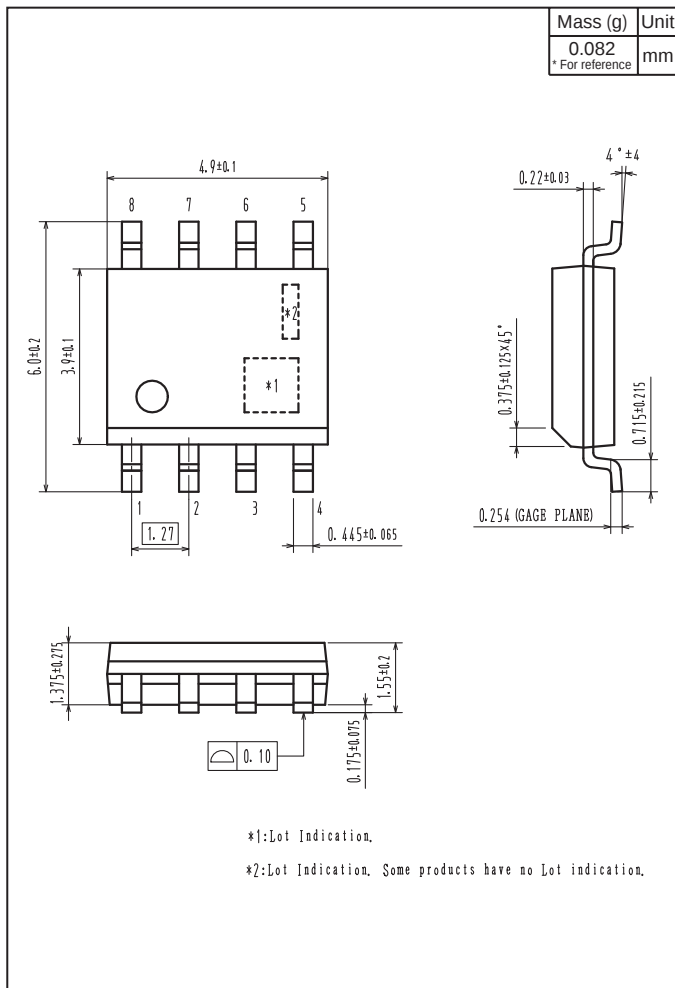


2-3. Leader portion and trailer portion (unit: mm)

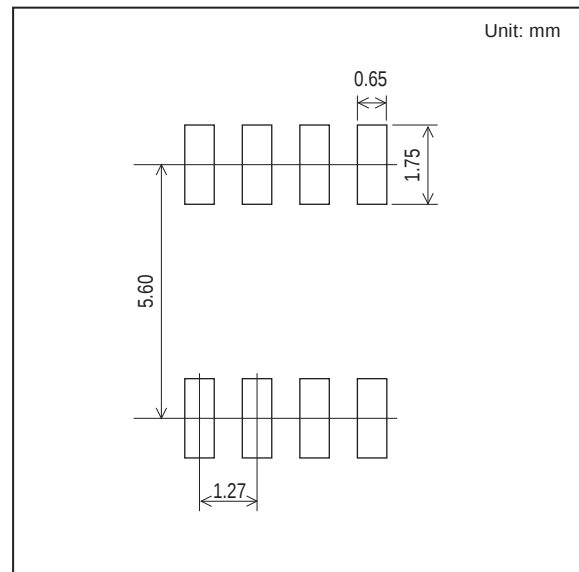


Outline Drawing

FW344A-TL-2W



Land Pattern Example



Note on usage : Since the FW344A is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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